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Please amend claims 20, 23, 25, 26, and 28 as follows. Please note that the amended claims are presented below in their amended form. They are further presented as an attachment to the amendments where the claims are shown using the conventional method of bracketing and underlining.

C2
Sub
ROR

20. (Amended) A process comprising the steps of:
preparing first and second electrodes opposed to each other in a reaction chamber, said first electrode having a plurality of gas inlets arranged in a first direction;
introducing a gas through said plurality of gas inlets into said reaction chamber;
generating a plasma of said reactive gas by applying a voltage between said first and second electrodes wherein said plasma extends from the first electrode toward the second electrode and a cross section of the plasma along planes of the first and second electrodes has a length along the first direction and a width along a second direction perpendicular to the first direction where the cross section is elongated in the first direction and the length is longer than the width;
placing a substrate between said first and second electrodes; and
changing a relative location of the substrate with the plasma in the second direction.

C3
Sub
ROR

23. (Amended) A process for comprising the steps of:
preparing first and second electrodes opposed to each other in a reaction chamber, said first electrode having a plurality of gas inlets arranged in a first direction;
introducing a gas through said plurality of gas inlets into said reaction chamber;
generating a plasma of said reactive gas by applying a voltage between said first and second electrodes wherein said first electrode is grounded;
placing a substrate adjacent to said second electrode;
forming a diamond-like carbon film on the substrate by plasma chemical vapor deposition using the plasma; and

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C3 sub
contd

moving said substrate while forming the diamond-like carbon film on the substrate in a second direction perpendicular to said first direction,
wherein the plasma extends from the first electrode toward the second electrode, and a region of the plasma is elongated more in the first direction than in the second direction.

C4 sub
contd

25. (Amended) A process comprising the steps of:
preparing first and second electrodes opposed to each other in a reaction chamber, said first electrode having a plurality of gas inlets arranged in a first direction;
introducing a gas through said plurality of gas inlets into said reaction chamber;
generating a plasma of said gas by applying a voltage between said first and second electrodes wherein said plasma has an elongated cross section along the first direction;
placing a substrate between said first and second electrodes; and
treating said substrate with said plasma while changing a relative location of the substrate with respect to the plasma in a second direction perpendicular to the first direction,
wherein a gap between said first and second electrodes is 30 mm or less, and the substrate is not in contact with the plasma during the treatment with the plasma.

26. (Amended) The process according to claim 25 wherein said gap is 10 mm or less.

C5 sub
contd

28. (Amended) A process comprising the steps of:
preparing first and second electrodes opposed to each other in a reaction chamber, said first electrode having at least one inlet having an opening elongated in a first direction;
introducing a gas through said inlet into said reaction chamber;
generating a plasma of said gas by applying a voltage between said first and second electrodes wherein said plasma extends from the first electrode toward the second electrode and a cross section of the plasma has a length along the first direction and a width along a second direction perpendicular to the first direction where the length is longer than the width;
placing a substrate between said first and second electrodes;

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cancel

treating said substrate with said plasma, and
changing a relative location of the substrate with respect to the plasma in the second
direction during the treatment with the plasma,
wherein a gap between said first and second electrodes is 30 mm or less.

Please add new claims 31-41 as follows:

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31. A process comprising the steps of:
preparing first and second electrodes opposed to each other in a reaction chamber, said
first electrode having at least one inlet having an opening elongated in a first direction;
introducing a gas through said inlet into said reaction chamber;
generating a plasma of said gas by applying a voltage between said first and second
electrodes wherein said plasma extends from the first electrode toward the second electrode and
a cross section of the plasma has a length along the first direction and a width along a second
direction perpendicular to the first direction where the length is longer than the width;
placing a substrate between said first and second electrodes;
forming a film on the substrate by plasma chemical vapor deposition by using the plasma,
and
changing a relative location of the substrate with respect to the plasma in the second
direction during the treatment with the plasma.

32. The process according to claim 31 wherein said gap is 10 mm or less.

33. The process according to claim 28 wherein a pressure in said reaction chamber is
from 0.1 to 800 Torr.

34. The process according to claim 20 wherein a film is formed on the substrate by
plasma chemical vapor deposition using the plasma.

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35. The process according to claim 20 wherein an ashing step is performed on the substrate by using the plasma.

36. The process according to claim 25 wherein a film is formed on the substrate by plasma chemical vapor deposition using the plasma.

37. The process according to claim 25 wherein an ashing step is performed on the substrate by using the plasma.

38. The process according to claim 28 wherein a film is formed on the substrate by plasma chemical vapor deposition using the plasma.

39. The process according to claim 28 wherein an ashing step is performed on the substrate by using the plasma.

40. The process according to claim 31 wherein a film is formed on the substrate by plasma chemical vapor deposition using the plasma.

41. The process according to claim 31 wherein an ashing step is performed on the substrate by using the plasma.--

REMARKS

Claims 20-41 are pending. By this Amendment, claims 1, 18 and 19 are cancelled, claims 20, 23, 25, 26 and 28 are amended and claims 31-41 are added. Reconsideration in view of the above amendments and the following remarks is respectfully requested.

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